Silicon NPN Power Transistors 2N6258

DESCRIPTION

- With TO-3 package
- Low collector-emitter saturation voltage

APPLICATIONS

- Designed for audio amplifier and switching circuits applications

PINNING

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	100	V
V_{CEO}	Collector-emitter voltage	Open base	80	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		30	A
I_B	Base current		7.5	A
P_D	Total Power Dissipation	T_C=25℃	250	W
T_j	Junction temperature		150	℃
T_{stg}	Storage temperature		-65~200	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
$R_{th\ j\text{-}c}$	Thermal resistance junction to case	0.875	℃/W

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CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-emitter sustaining voltage	I_C=0.2A ;I_B=0	80			V
V_{CEsat}	Collector-emitter saturation voltge	I_C=7.5A ;I_B=0.75A			1.0	V
V_{BEsat}	Base-emitter saturation voltage	I_C=7.5A ;I_B=0.75A			1.3	V
I_{CEO}	Collector cut-off current	V_{CE}=40V; I_B=0			1.0	mA
I_{CEV}	Collector cut-off current	V_{CE}=100V; $V_{BE(off)}$=1.5V T_C=150℃			0.1 5.0	mA
I_{CBO}	Emitter cut-off current	V_{CB}=100V; I_E=0			0.1	mA
I_{EBO}	Emitter cut-off current	V_{EB}=5V; I_C=0			0.1	mA
h_{FE}	DC current gain	I_C=15A ; V_{CE}=2V	20			
f_T	Transition frequency	I_C=1A;V_{CE}=10V	0.8			MHz

PACKAGE OUTLINE

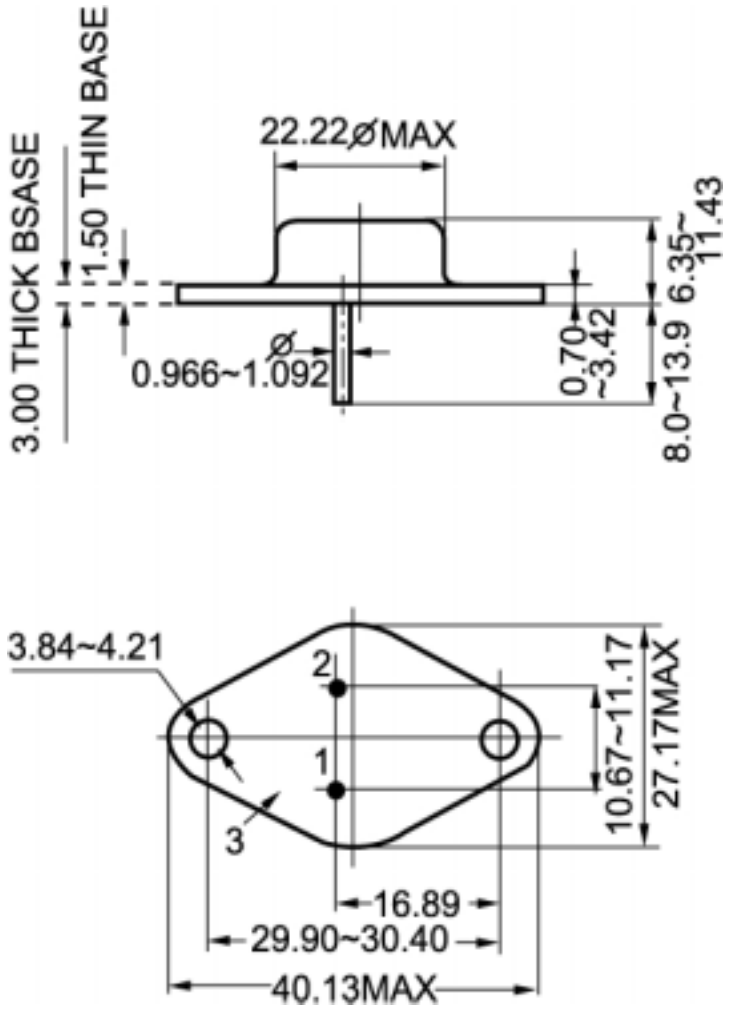

Fig.2 outline dimensions (unindicated tolerance:±0.10mm)